High Light Extraction Efficiency III-Nitride LED
Tech ID: 25553 / UC Case 2008-277-0

BRIEF DESCRIPTION
A III-nitride light emitting diode (LED) with increased light extraction from having at least one textured surface of a semipolar or nonpolar plane of a III-nitride layer of the LED.

BACKGROUND
While the advent of high-quality freestanding GaN substrates has led to the development of high-performance nonpolar and semipolar LEDs, there is plenty of room for improving the light extraction efficiency. The lack of means for surface roughening has become a major hurdle for nonpolar and semipolar LEDs to achieve higher extraction efficiency and hence higher overall efficiency, and therefore improved roughening techniques are needed to address this issue.

DESCRIPTION
Researchers at the University of California, Santa Barbara have developed a III-nitride light emitting diode (LED) with increased light extraction from having at least one textured surface of a semipolar or nonpolar plane of a III-nitride layer of the LED. The texturing may be performed by plasma-assisted chemical etching, photolithography followed by etching, or nano-imprinting followed by etching.

ADVANTAGES
▶ Increased light extraction efficiency and output power
▶ More straightforward than other light extraction enhancement techniques (such as using a photonic crystal)
▶ Applicable to all nitride semiconductor surfaces regardless of crystal structure

APPLICATIONS
▶ LEDs

PATENT STATUS

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<th>Type</th>
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<td>United States Of America</td>
<td>Issued Patent</td>
<td>9,040,326</td>
<td>05/26/2015</td>
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<td>United States Of America</td>
<td>Issued Patent</td>
<td>8,114,698</td>
<td>02/14/2012</td>
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CATEGORIZED AS
▶ Engineering
▶ Energy
▶ Lighting
▶ Other
▶ Semiconductors
▶ Design and Fabrication

RELATED CASES
2008-277-0

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS
▶ Enhanced Optical Polarization of Nitride LEDs by Increased Indium Incorporation
▶ Etching Technique for the Fabrication of Thin (Al, In, Ga)N Layers
▶ Lateral Growth Method for Defect Reduction of Semipolar Nitride Films
▶ Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
▶ III-Nitride-Based Devices Grown With Relaxed Active Region
▶ Low-Cost Zinc Oxide for High-Power-Output, GaN-Based LEDs (UC Case 2010-183)
▶ Defect Reduction in GaN films using in-situ SiNx Nanomask
▶ Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
▶ Highly Efficient Blue-Violet III-Nitride Semipolar Laser Diodes
▶ Hybrid Growth Method for Improved III-Nitride Tunnel Junction Devices
▶ Low Temperature Deposition of Magnesium Doped Nitride Films
▶ Transparent Mirrorless (TML) LEDs
- Improved GaN Substrates Prepared with Ammonothermal Growth
- Optimization of Laser Bar Orientation for Nonpolar Laser Diodes
- Size-Independent Forward Voltage Micro-LED with an Epitaxial Junction
- Method for Enhancing Growth of Semipolar Nitride Devices
- III-Nitride Tunnel Junction with Modified Interface
- Growth of Polyhedron-Shaped Gallium Nitride Bulk Crystals
- Nonpolar III-Nitride LEDs With Long Wavelength Emission
- Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
- Growth of High-Quality, Thick, Non-Polar M-Plane GaN Films
- Increased Light Extraction with Multistep Deposition of ZnO on GaN
- Method for Manufacturing Improved III-Nitride LEDs and Laser Diodes: Monolithic Integration of Optically Pumped and Electrically Injected III-Nitride LEDs
- Selective-Area Mesoporous Semiconductors And Devices For Optoelectronic And Photonic Applications
- High-Efficiency, Mirrorless Non-Polar and Semi-Polar Light Emitting Devices
- Method for Growing High-Quality Group III-Nitride Crystals
- Controlled Photoelectrochemical (PEC) Etching by Modification of Local Electrochemical Potential of Semiconductor Structure
- Oxyfluoride Phosphors for Use in White Light LEDs
- Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
- (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- Thermally Stable, Laser-Driven White Lighting Device
- MOCVD Growth of Planar Non-Polar M-Plane Gallium Nitride
- Reduced Dislocation Density of Non-Polar GaN Grown by Hydride Vapor Phase Epitaxy
- Highly Compact, High-Index Dielectric Nanostructures for Deep-Ultraviolet Devices
- Reduction in Leakage Current and Increase in Efficiency of III-Nitride MicroLEDs
- Methods for Fabricating III-Nitride Tunnel Junction Devices
- Low-Droop LED Structure on GaN Semi-polar Substrates
- Contact Architectures for Tunnel Junction Devices
- Semi-polar LED/LD Devices on Relaxed Template with Misfit Dislocation at Hetero-interface
- Photoelectrochemical Etching Of P-Type Semiconductor Heterostructures
- Semipolar-Based Yellow, Green, Blue LEDs with Improved Performance
- III-Nitride-Based Devices Grown On Thin Template On Thermally Decomposed Material
- Growth of Semipolar III-V Nitride Films with Lower Defect Density
- III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- Improved Manufacturing of Solid State Lasers via Patternning of Photonic Crystals
- High Efficiency III-Nitride Devices with Smooth Relaxed InGaN Buffer and Strain Compliant Template
- Tunable White Light Based on Polarization-Sensitive LEDs
- Cleaved Facet Edge-Emitting Laser Diodes Grown on Semipolar GaN
- Growth of High-Performance M-plane GaN Optical Devices
- Packaging Technique for the Fabrication of Polarized Light Emitting Diodes
- Improved Anisotropic Strain Control in Semipolar Nitride Devices
- III-V Nitride Device Structures on Patterned Substrates
- Activation of P-Type Layers of Tunnel Junctions in Micro-LEDs
- Method for Increasing GaN Substrate Area in Nitride Devices
- Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- Growth of Planar, Non-Polar, A-Plane GaN by Hydride Vapor Phase Epitaxy
- GaN-Based Thermoelectric Device for Micro-Power Generation
- Limiting Strain-Relaxation in III-Nitride Heterostructures by Substrate Patternning
- LED Device Structures with Minimized Light Re-Absorption
- Growth of Planar Semi-Polar Gallium Nitride
- Nonpolar (Al, In, Ga)N Quantum Well Design
- UV Optoelectronic Devices Based on Nonpolar and Semi-polar AllnP and AllInGaN Alloys
- Defect Reduction of Non-Polar and Semi-Polar III-Nitrides
- III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture
- Enhancing Growth of Semipolar (Al,In,Ga,B)N Films via MOCVD